1:00 PM - 1:30 PM

[19p-B5-1][JSAP Paper Award Speech](30 min.) Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport

Yoshinao Kumagai, Yuki Kubota, Toru Nagashima, Toru Kinoshita, Rafael Dalmau, Raoul Schlesser, Baxter Moody, Jinqiao Xie, Hisashi Murakami, Akinori Koukitu, Zlatko Sitar (TUAT, TOKUYAMA, HexaTech, NC State Univ.)